

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE4953 uses advanced trench technology to provide excellent $R_{\rm DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

• $V_{DS} = -30V, I_D = -5.1A$

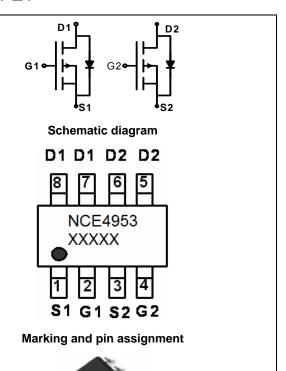
 $R_{DS(ON)}$ < 90m Ω @ V_{GS} =-4.5V

 $R_{DS(ON)} < 55 m\Omega$ @ V_{GS} =-10V

- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



SOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE4953	NCE4953	SOP-8	Ø330mm	12mm	4000 units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	V _G S	±20	V
Drain Current-Continuous	I _D	-5.1	Α
Drain Current-Pulsed (Note 1)	I _{DM}	-20	А
Maximum Power Dissipation	P _D	2.5	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$ C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	50	°C/W
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Electrical Characteristics (T_A=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						



NCE4953

Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V,V _{GS} =0V	-	-	-1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =-250μA	-1.1	-1.6	-2.1	V
Daile On the October Providence	_	V _{GS} =-10V, I _D =-5.1A	-	43	55	mΩ
Drain-Source On-State Resistance	$R_{DS(ON)}$	V _{GS} =-4.5V, I _D =-4.2A	-	62	90	mΩ
Forward Transconductance	g Fs	V _{DS} =-15V,I _D =-4.5A	4	7	-	S
Dynamic Characteristics (Note4)	1	-	I.	·	·	
Input Capacitance	C _{lss}	451/1/ 01/		520	-	PF
Output Capacitance	C _{oss}	V _{DS} =-15V,V _{GS} =0V,		130	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	70	-	PF
Switching Characteristics (Note 4)	•	•	I.	·		l
Turn-on Delay Time	t _{d(on)}		-	7	-	nS
Turn-on Rise Time	t _r	V _{DD} =-15V, ID=-1A,	-	13	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10V, R_{GEN} =6 Ω	-	14	-	nS
Turn-Off Fall Time	t _f		-	9	-	nS
Total Gate Charge	Qg	V _{DS} =-15V,I _D =-5.1A,V _{GS} =-10V	-	11	-	nC
Gate-Source Charge	Q _{gs}		-	2.2	-	nC
Gate-Drain Charge	Q _{gd}		-	3	-	nC
Drain-Source Diode Characteristics		1	I	1	I	1
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-5.1A	-	-	-1.2	V
	1	1				

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

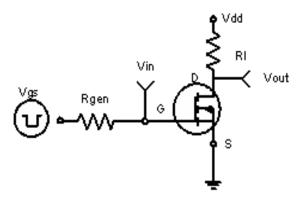


Figure 1:Switching Test Circuit

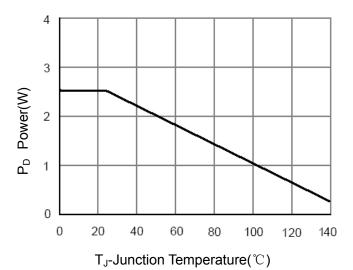


Figure 3 Power Dissipation

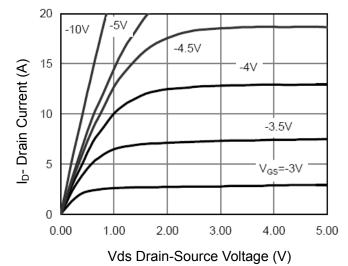


Figure 5 Output Characteristics

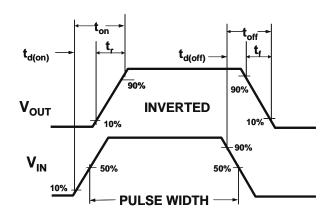


Figure 2:Switching Waveforms

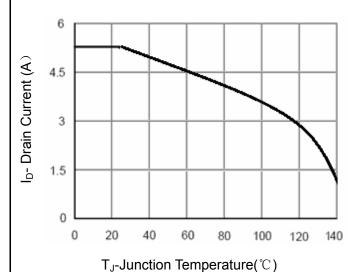


Figure 4 Drain Current

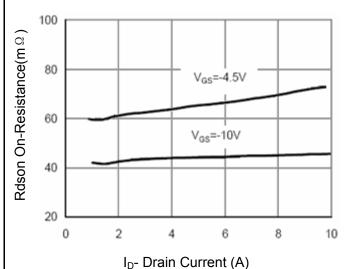
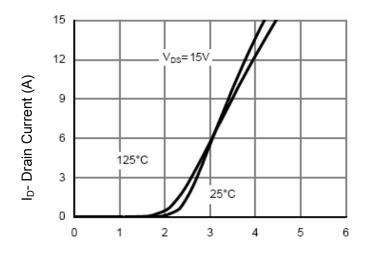
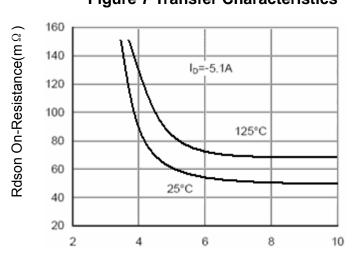


Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

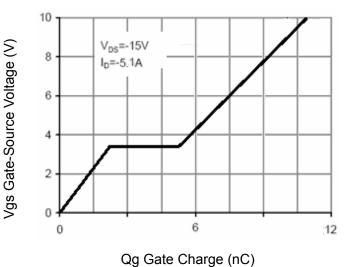


Figure 11 Gate Charge

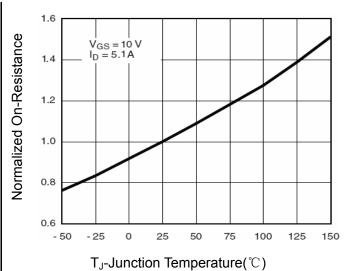


Figure 8 Drain-Source On-Resistance

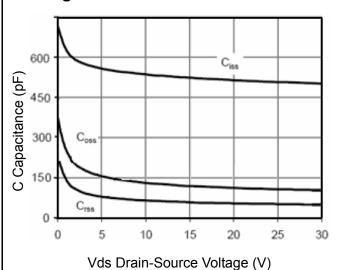


Figure 10 Capacitance vs Vds

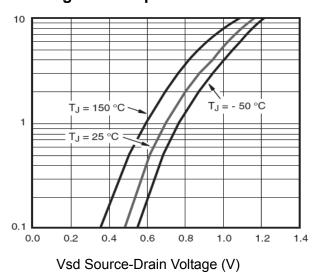
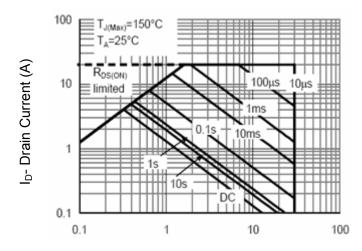


Figure 12 Source- Drain Diode Forward

Is- Reverse Drain Current (A)





Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area

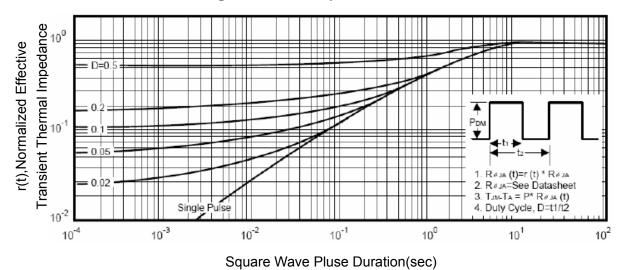
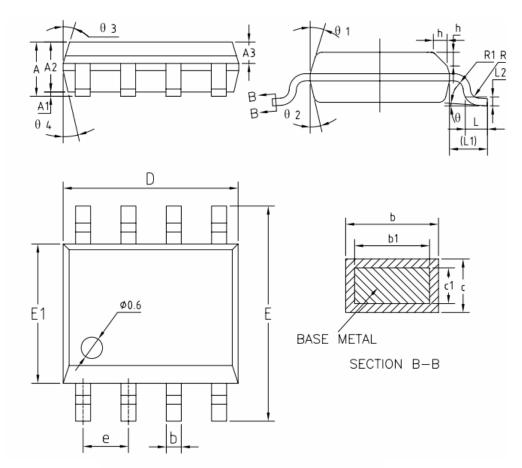


Figure 14 Normalized Maximum Transient Thermal Impedance



SOP-8 Package Information



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX		
Α	1.35	1.55	1.75		
A1	0.10	0.15	0.25		
A2	1.25	1.40	1.65		
A3	0.50	0.60	0.70		
b	0.38	_	0.51		
b1	0.37	0.42	0.47		
С	0.18	_	0.25		
c1	0.17	0.20	0.23		
D	4.80	4.90	5.00		
E	5.80	6.00	6.20		
E1	3.80	3.90	4.00		
e	1.17	1.27	1.37		
L	0.45	0.60	0.80		
L1	1.04REF				
L2	0.25BSC				
R	0.07	_	_		
R1	0.07	_	_		
h	0.30	0.40	0.50		
θ	ò	-	8*		
θ 1	15*	17*	19*		
θ2	11"	13*	15*		
θ3	15*	17'	19°		
θ 4	11"	13*	15 °		



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